

LISTING OF AND AMENDMENTS TO CLAIMS:

1. - 9. (canceled)

10. (original) A method for manufacturing an active matrix substrate in which a source electrode, a drain electrode, a semiconductor layer, a gate insulating film and a gate electrode are sequentially deposited on an insulating substrate directly or indirectly, comprising the steps of:

    patterning a gate metal deposited on said gate insulating film by the use of a resist mask;

    patterning said gate insulating film and said semiconductor layer by using said patterned gate metal as a mask;

    forming an ITO film and patterning the ITO film by using a resist mask; and

    patterning said gate electrode by using said patterned ITO film as a mask.

11. (original) The method according to claim 10, wherein the step of patterning said ITO film includes a step of patterning said ITO film in consideration of a pattern of said gate electrode as well as forming a pattern of a pixel electrode.

12. (original) The display device according to claim 11, wherein the step of forming said ITO film is formed in the same step of forming an ITO film constituting said pixel electrode.

13. (original) The method according to claim 11, wherein the step of patterning said ITO film includes a step for patterning said ITO film in consideration of a pattern of a gate line connected to said gate electrode.

14. (original) A method of manufacturing an active matrix substrate comprising the steps of:

forming a pattern of a gate electrode on an insulating substrate;

sequentially depositing a gate insulating film and a semiconductor layer on said gate electrode and then forming a metal film;

depositing an ITO film in consideration of a pattern of said metal film to be patterned and in consideration of a pattern of a pixel electrode; and

patterning said metal film by using said ITO film as a mask thus forming a source electrode and a drain electrode.

15. (original) The method according to claim 14, further comprising the step of:

providing a protection film on said source and drain electrodes to interpose the ITO film therebetween, and patterning said semiconductor layer by using said protection film.

16. (original) The method according to claim 14, further comprising the step of:

forming a pattern of a data line by using said ITO film as a mask in the step of forming said source electrode and said drain electrode.

17. (original) The method according to claim 14, wherein the step of forming said metal film is for forming said metal film in the same pattern as that of the patterned gate insulating film.

18. (canceled)